

SOD-123FL Plastic-Encapsulate Diodes

General Purpose Rectifier

Features

- •lo
- •VRRM 50V-1000V
- High surge current capability

1A

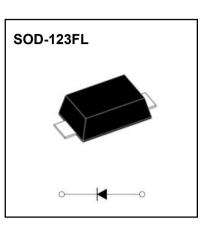
- •Glass passivated chip
- Polarity: Color band denotes cathode

Applications

Rectifier

Marking

• DSR1A-DSR1M : A1-A7



Limiting Values (Absolute Maximum Rating)

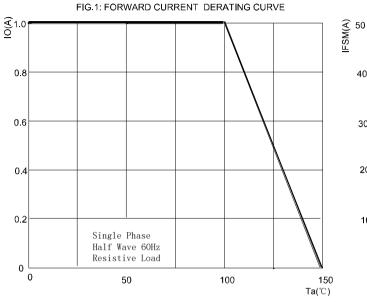
ltem	Symbol	Unit	Conditions	DSR1						
item			Conditions	А	В	D	G	J	К	М
Repetitive Peak Reverse Voltage	V _{RRM}	V		50	100	200	400	600	800	1000
Maximum RMS Voltage	V _{RMS}	V		35	70	140	280	420	560	700
Average Forward Current	I _{F(AV)}	А	60Hz Half sine wave, Resistance load, Ta(Fig.1)	1.0						
Surge(Non-repetitive)Forward Current	I _{FSM}	A	60Hz Half-sine wave,1 cycle, Ta=25℃	30						
Junction Temperature	TJ	°C		-55~+ 150						
Storage Temperature	T _{STG}	°C		-55 ~ +150						

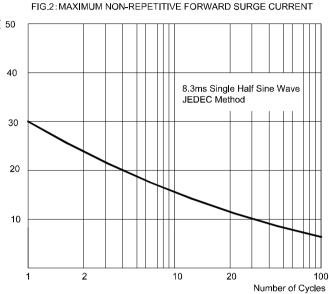
Electrical Characteristics (Ta=25 $^{\circ}$ C Unless otherwise specified)

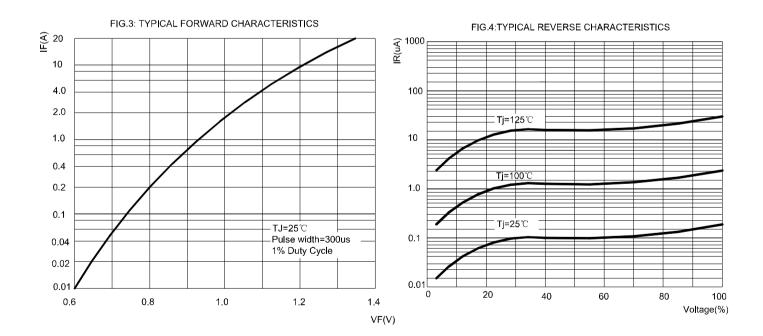
ltem	Symbol	Unit	Test Condition		Мах
Peak Forward Voltage	V _{FM}	V I _{FM} =1.0A		1.0	
Peak Reverse Current	IRRM1	μA	V _{RM} =V _{RRM}	Ta=25℃	10
	I RRM2			T _a =125℃	50
Thermal Resistance(Typical)	$R_{\theta_{J}-A}$	°C/W	Between junction and ambient		70 ¹⁾
	R _{θJ-L}		Between junction and lead		25 ¹⁾

Notes:

(1) Thermal resistance between junction and ambient and between junction and lead mounted on P.C.B with 3mm*3mm copper pad areas.

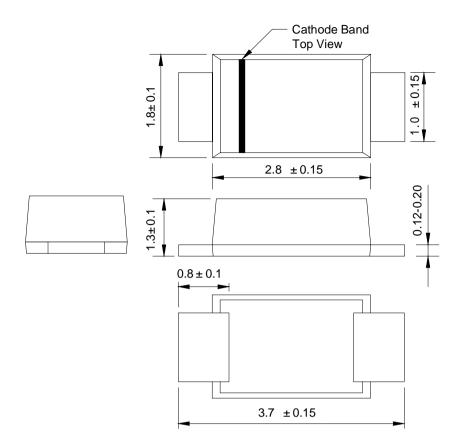






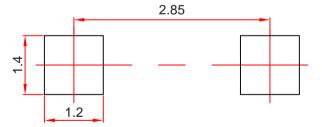
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SOD-123FL Package Outline Dimensions



Dimensions in millimeters

SOD-123FL Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.

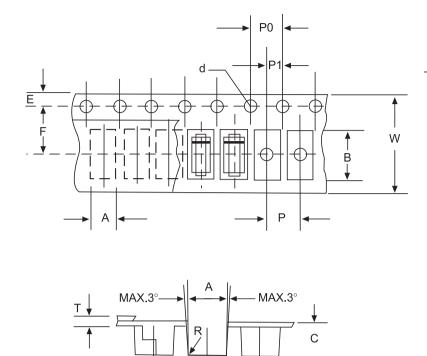
3. The pad layout is for reference purposes only.

NOTICE

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Reel Taping Specifications For Surface Mount Devices-SOD-123FL



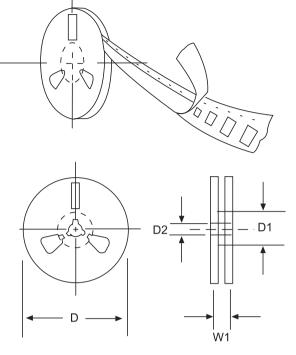


FIG:CONFIGURATION OF AXIAL TAPING

ITEM	SYMBOL	SOD-123FLmm(inch)
Carrier width	А	2.05±0.1(0.081±0.004)
Carrier length	В	3.95±0.1(0.156±0.004)
Carrier depth	С	1.45±0.1(0.057±0.004)
Sprocket hole	d	1.55±0.05(0.061±0.002)
Reel outside diameter	D	280/178±2.0(11/7.0±0.079)
Reel inner diameter	D1	50±0.2(1.969±0.008)
Feed hole diameter	D2	13±0.5(0.512±0.020)
Strocket hole position	E	1.75±0.1(0.069±0.004)
Punch hole position	F	3.50±0.1(0.138±0.002)
Punch hole pitch	Р	4.0±0.1(0.157±0.004)
Sprocket hole pitch	P0	4.0±0.1(0.157±0.004)
Embossment center	P1	2.0±0.1(0.079±0.004)
Totall tape thickness	Т	0.21±0.25(0.008±0.010)
Tape width	W	8.0±0.2(0.315±0.008)
Reel width	W1	10.0±2.0(0.394±0.079)

NOTE: Devices are packde in accordance with EIA standard RS-481-A and specification given above.

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